

ZXMD63P03X

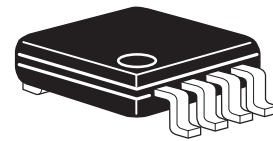
DUAL 30V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -30V$; $R_{DS(ON)} = 0.185V$; $I_D = -2.0A$

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



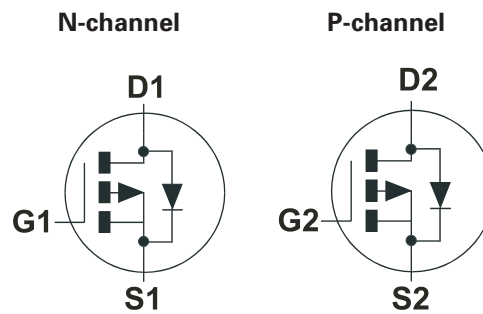
MSOP8

FEATURES

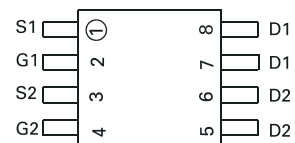
- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control



Pin-out



Top view

ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXMD63P03XTA	7	12 embossed	1,000
ZXMD63P03XTC	13	12 embossed	4,000

DEVICE MARKING

ZXM63P03

ZXMD63P03X

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	P-CHANNEL	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($V_{GS}=4.5V$; $T_A=25^\circ C$)(b)(d) ($V_{GS}=4.5V$; $T_A=70^\circ C$)(b)(d)	I_D	2.0 1.6	A A
Pulsed Drain Current (c)(d)	I_{DM}	-9.6	A
Continuous Source Current (Body Diode)(b)(d)	I_S	-1.4	A
Pulsed Source Current (Body Diode)(c)(d)	I_{SM}	-9.6	A
Power Dissipation at $T_A=25^\circ C$ (a)(d) Linear Derating Factor	P_D	0.87 6.9	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (a)(e) Linear Derating Factor	P_D	1.04 8.3	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b)(d) Linear Derating Factor	P_D	1.25 10	W mW/ $^\circ C$
Operating and Storage Temperature Range	T_j : T_{stg}	-55 to +150	$^\circ C$

THERMAL RESISTANCE

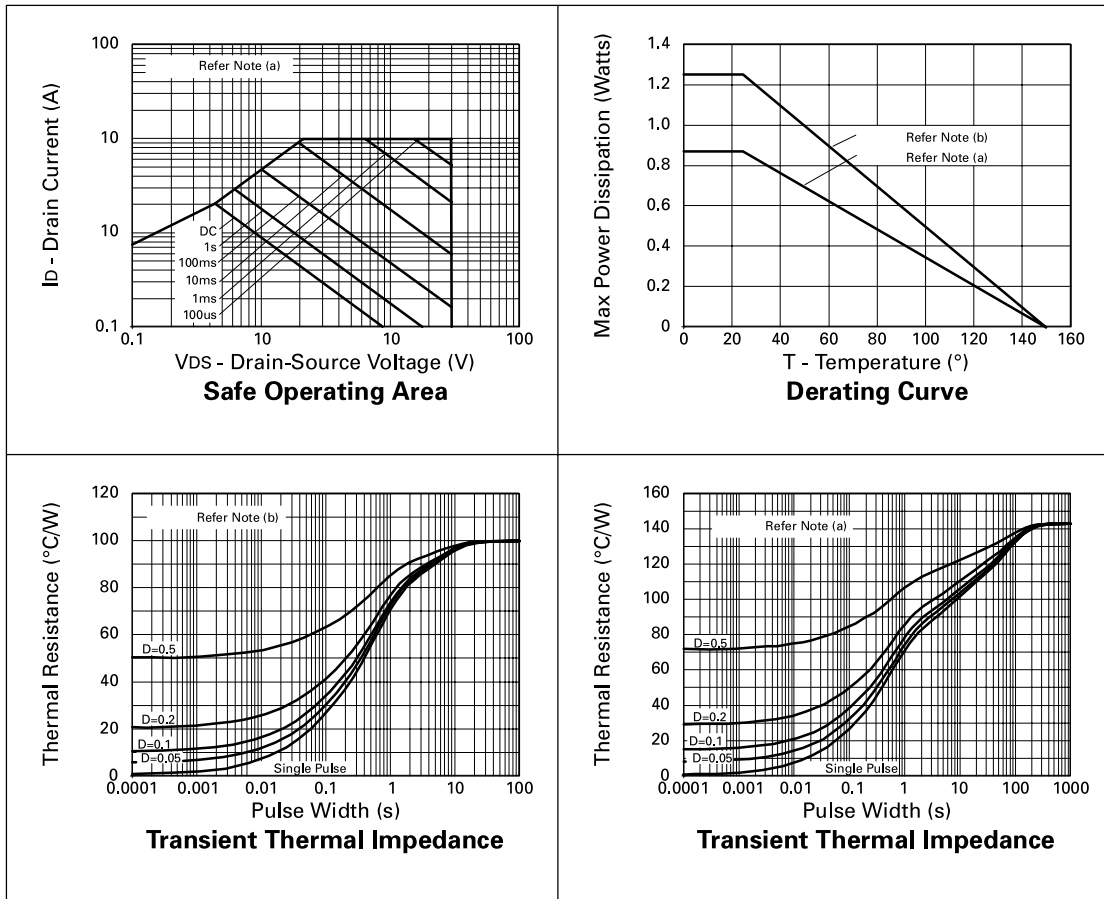
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	143	$^\circ C/W$
Junction to Ambient (b)(d)	$R_{\theta JA}$	100	$^\circ C/W$
Junction to Ambient (a)(e)	$R_{\theta JA}$	120	$^\circ C/W$

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
- (b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.
- (c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
- (d) For device with one active die.
- (e) For device with two active die running at equal power.

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CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

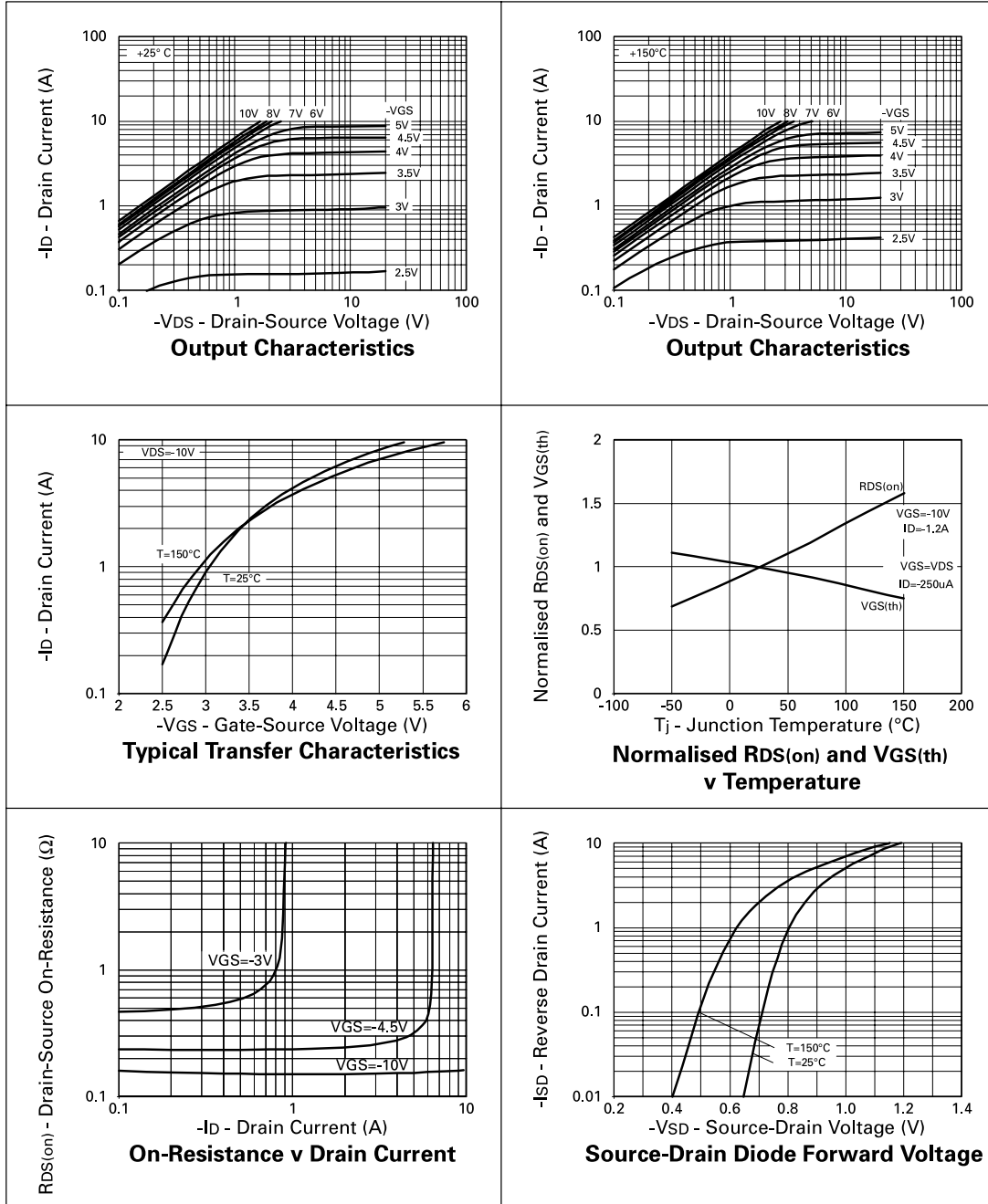
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			-1	μA	$V_{DS} = -30\text{V}$, $V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}			± 100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}$, $V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.185 0.27	Ω	$V_{GS} = -10\text{V}$, $I_D = -1.2\text{A}$ $V_{GS} = -4.5\text{V}$, $I_D = -0.6\text{A}$
Forward Transconductance (3)	g_{fs}	0.92			S	$V_{DS} = -10\text{V}$, $I_D = -0.6\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		270		pF	$V_{DS} = -25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$
Output Capacitance	C_{oss}		80		pF	
Reverse Transfer Capacitance	C_{rss}		30		pF	
SWITCHING (2) (3)						
Turn-On Delay Time	$t_{d(on)}$		2.6		ns	$V_{DD} = -15\text{V}$, $I_D = -1.2\text{A}$ $R_G = 6.2\Omega$, $R_D = 6.2\Omega$ (Refer to test circuit)
Rise Time	t_r		4.8		ns	
Turn-Off Delay Time	$t_{d(off)}$		13.1		ns	
Fall Time	t_f		9.3		ns	
Total Gate Charge	Q_g			7	nC	$V_{DS} = -24\text{V}$, $V_{GS} = -10\text{V}$, $I_D = -1.2\text{A}$ (Refer to test circuit)
Gate-Source Charge	Q_{gs}			1.2	nC	
Gate Drain Charge	Q_{gd}			2	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			-0.95	V	$T_j = 25^{\circ}\text{C}$, $I_S = -1.2\text{A}$, $V_{GS} = 0\text{V}$
Reverse Recovery Time (3)	t_{rr}		21.4		ns	$T_j = 25^{\circ}\text{C}$, $I_F = -1.2\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge(3)	Q_{rr}		15.7		nC	

NOTES:

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle @2% .
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.

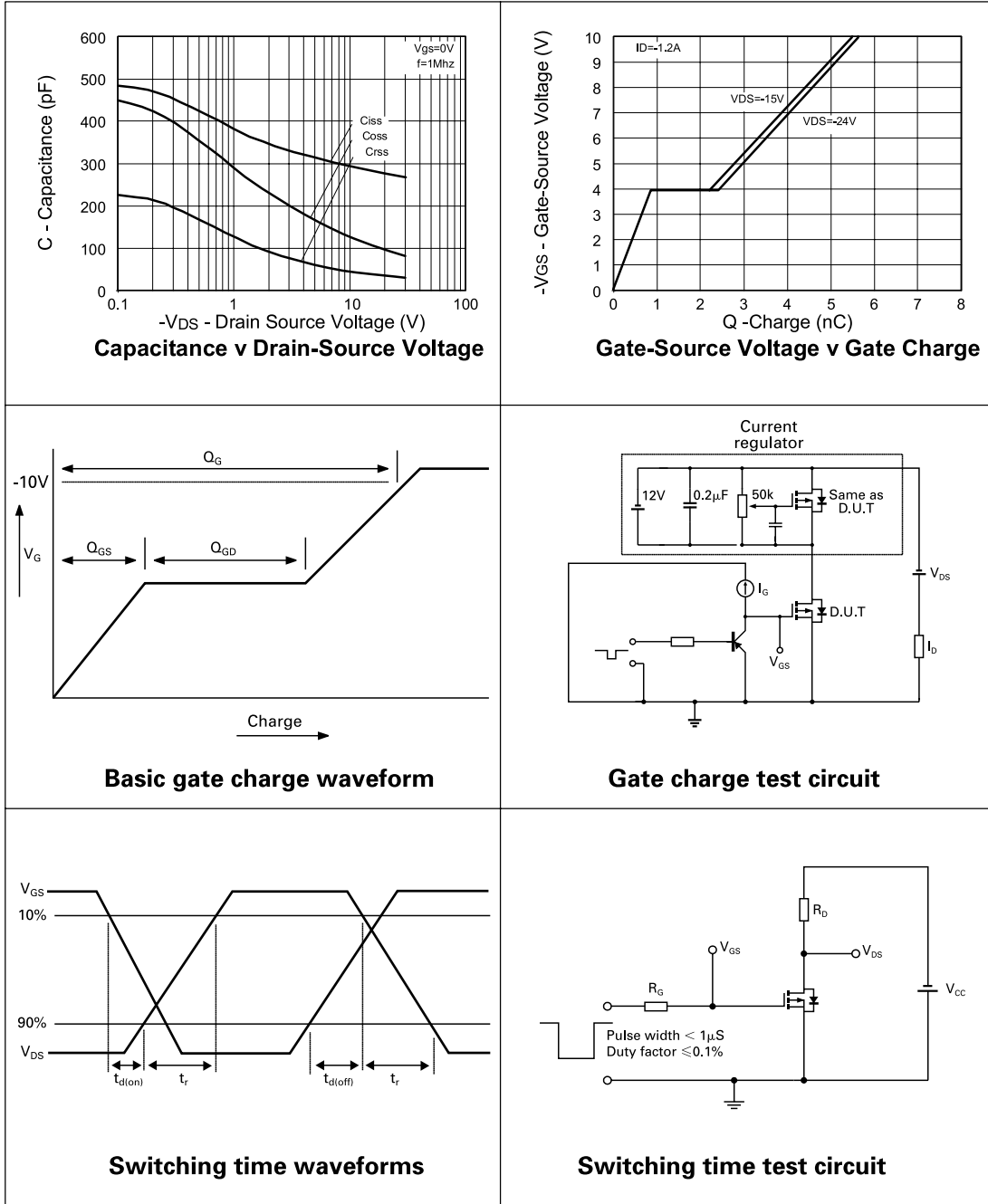
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TYPICAL CHARACTERISTICS



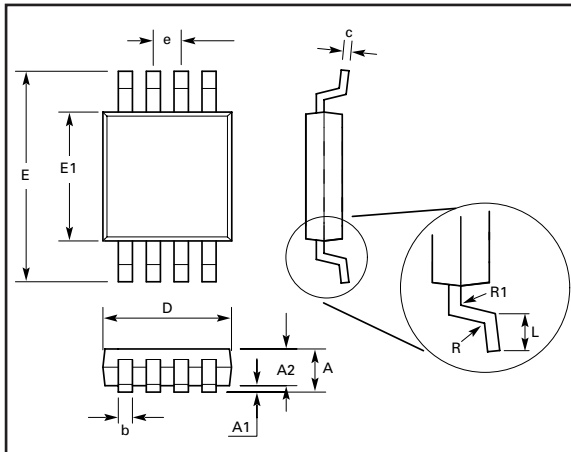
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TYPICAL CHARACTERISTICS

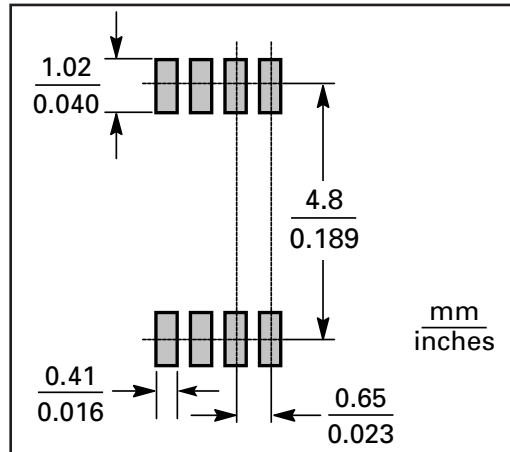


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PACKAGE DETAILS



PAD LAYOUT DETAILS



PACKAGE DIMENSIONS

DIM	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.91	1.11	0.036	0.044
A1	0.10	0.20	0.004	0.008
B	0.25	0.36	0.010	0.014
C	0.13	0.18	0.005	0.007
D	2.95	3.05	0.116	0.120
e	0.65NOM		0.0256	
e1	0.33NOM		0.0128	
E	2.95	3.05	0.116	0.120
H	4.78	5.03	0.188	0.198
L	0.41	0.66	0.016	0.026
θ°	0°	6°	0°	6°

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park Chadderton, Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europa.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

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